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Applied Surface Science 100/101 (1996) 660-668

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Author index

- Abe, S., see Yea, B. 100/101 (1996) 365
Adachi, H., see Satoh, H. 100/101 (1996) 216
Adachi, H., see Endo, M. 100/101 (1996) 378
Adachi, M., see Uchida, H. 100/101 (1996) 399
Aizawa, T., see Oyoshi, K. 100/101 (1996) 374
Akiya, S., see Homma, T. 100/101 (1996) 189
Ando, Y., see Yamada, T. 100/101 (1996) 287
Aoki, T., see Hatanaka, Y. 100/101 (1996) 621
Aoyama, T., M. Tanemura and F. Okuyama,
Angular distribution of particles sput-
tered from GaAs by Ar⁺ and Xe⁺ ion
bombardment 100/101 (1996) 351
Arafune, R., see Sakamoto, K. 100/101 (1996) 124
Arakawa, T., see Iwaso, M. 100/101 (1996) 147
Asada, H., see Kawano, H. 100/101 (1996) 174
Asakura, K., see Chun, W.-J. 100/101 (1996) 143
Awaji, N., see Sugita, Y. 100/101 (1996) 268
Ayame, A., see Tomizuka, H. 100/101 (1996) 243

Baba, Y., see Yamamoto, H. 100/101 (1996) 333
Badaye, M., see Pindoria, G. 100/101 (1996) 347
Block, J.H., see Kawada, H. 100/101 (1996) 587
Bodnar, S., see Regolini, J.L. 100/101 (1996) 566
Bohr, M.T., Technology development
strategies for the 21st century 100/101 (1996) 534
Bruckbauer, A., see Futamata, M. 100/101 (1996) 60
Bryantseva, T.A., D.V. Lioubtchenko and
V.V. Lopatin, Ga migration process in
Au film on (100) GaAs under tempera-
ture treatment in vacuum 100/101 (1996) 169
Butcher, K.S.A., see Zhou, B. 100/101 (1996) 643

Chen, B.-Y., J.-R. Chen, F.-L. Jenq and
C.-S. Hong, A theoretical analysis of
temperature dependence on hydro-
genated amorphous silicon thin-film
transistors with the consideration of re-
sistance of the a-Si:H film layer as a
function of temperature 100/101 (1996) 601
Chen, C.H., see Chen, W.D. 100/101 (1996) 530
Chen, J.-R., see Chen, B.-Y. 100/101 (1996) 601
Chen, W.D. and Y.D. Cui, Determination of
Al_xGa_{1-x}As Auger sensitivity factors 100/101 (1996) 156
Chen, W.D., X.L. Xie, Y.D. Cui, C.H. Chen
and C.C. Hsu, Microstructure studies of
PdGe/Ge ohmic contacts to n-type
GaAs formed by rapid thermal anneal-
ing 100/101 (1996) 530
Chen, W.D., X.Q. Li, L.H. Duan, X.L. Xie
and Y.D. Cui, Photoluminescence en-
hancement of (NH₄)₂S_x passivated InP
surface by rapid thermal annealing 100/101 (1996) 592
Chew, A., see Sykes, D.E. 100/101 (1996) 77
Chiwaki, M., see Ohdaira, T. 100/101 (1996) 73
Chiwaki, M., see Suzuki, R. 100/101 (1996) 297
Chun, W.-J., K. Asakura and Y. Iwasawa,
Surface structure analysis of dispersed
metal sites on single crystal metal ox-
ides by means of polarization-dependent
total- reflection fluorescent EXAFS 100/101 (1996) 143
Cox, N., see Numajiri, K. 100/101 (1996) 541
Cui, Y.D., see Chen, W.D. 100/101 (1996) 156
Cui, Y.D., see Chen, W.D. 100/101 (1996) 530
Cui, Y.D., see Chen, W.D. 100/101 (1996) 592
Czuba, P., see Szymonski, M. 100/101 (1996) 102

Ding, Z.-J., R. Shimizu and K. Goto, Intrinsic
Auger signal profiles derived by
Monte Carlo analysis 100/101 (1996) 15
Du Plessis, J. and E.C. Viljoen, Sn segrega-
tion to the low index surfaces of a cop-
per single crystal 100/101 (1996) 222
Duan, L.H., see Chen, W.D. 100/101 (1996) 592

Ebina, A., see Takeuchi, T. 100/101 (1996) 596
Egawa, T., see Uchida, H. 100/101 (1996) 399
Egawa, T., see Hasegawa, Y. 100/101 (1996) 482
Emoto, T., K. Komatsu, A. Ichimiya, S.
Ninomiya and M. Sekiguchi, Soft X-ray
emissions by highly charged ions on
solid surfaces: Mo and Ta surfaces 100/101 (1996) 355
Endo, M., H. Nakane and H. Adachi, Field
emission from transition metal nitride 100/101 (1996) 378
Enta, Y., Y. Takegawa, M. Suemitsu and N.
Miyamoto, Growth kinetics of thermal
oxidation process on Si(100) by real
time ultraviolet photoelectron spec-
troscopy 100/101 (1996) 449

Fukuda, Y., see Murata, J. 100/101 (1996) 417
Furukawa, T., see Inanaga, K. 100/101 (1996) 421

- Furuya, M., M. Soga and H. Takano, Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS 100/101 (1996) 508
- Futamata, M., E. Keim, A. Bruckbauer, D. Schumacher and A. Otto, Enhanced Raman scattering from copper phthalocyanine on Pt by use of a Weierstrass prism 100/101 (1996) 60
- Gaidarova, V., see Takeichi, Y. 100/101 (1996) 25
- Ganjoo, A., see Yoshida, A. 100/101 (1996) 491
- Gheyas, S.I., M. Nishio, T. Urisu and H. Ogawa, Adsorption and thermal decomposition of diethyltellurium on GaAs(100) 100/101 (1996) 211
- Gheyas, S.I., S. Hirano, M. Nishio and H. Ogawa, Aluminum doping of ZnTe grown by MOVPE 100/101 (1996) 634
- Gheyas, S.I., S. Hirano, M. Nishio and H. Ogawa, Growth of high-quality ZnTe layers by MOVPE 100/101 (1996) 647
- Gnaser, H., Processes in low-energy ion-surface collisions: preferential sputtering, defect and adatom formation 100/101 (1996) 316
- Goto, K., see Ding, Z.-J. 100/101 (1996) 15
- Goto, K., see Takeichi, Y. 100/101 (1996) 25
- Gotoh, Y., see Tsuji, H. 100/101 (1996) 342
- Gotoh, Y., see Toyota, Y. 100/101 (1996) 360
- Gotoh, Y., see Ishikawa, J. 100/101 (1996) 370
- Goya, T., see Numajiri, K. 100/101 (1996) 541
- Graat, P.C.J. and M.A.J. Somers, Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra 100/101 (1996) 36
- Gries, W.H., A general procedure for extracting quantitative depth information from take-off-angle-resolved XPS and AES 100/101 (1996) 41
- Gruyters, M., see Mitrelias, T. 100/101 (1996) 305
- Gutleben, C.D., see Kita, A. 100/101 (1996) 652
- Harada, T., see Kitada, T. 100/101 (1996) 89
- Harsdorff, M., see Heyn, Ch. 100/101 (1996) 494
- Hasebe, Y., see Yamauchi, S. 100/101 (1996) 522
- Hasegawa, M., see Ohdaira, T. 100/101 (1996) 73
- Hasegawa, M., see Kobayashi, N. 100/101 (1996) 498
- Hasegawa, Y., T. Egawa, T. Jimbo and M. Umeno, GaAs-based LED on Si substrate with GaAs islands active region by droplet-epitaxy 100/101 (1996) 482
- Hashimoto, Y., see Horio, Y. 100/101 (1996) 292
- Hatakeyama, M., I. Nagahama, K. Ichiki, M. Nakao and Y. Hatamura, New-type focused fast atom beam (F-FAB) source and evaluation of emitted beam density distribution 100/101 (1996) 277
- Hatamura, Y., see Hatakeyama, M. 100/101 (1996) 277
- Hatanaka, Y., T. Aoki, M. Morita and Y. Nakanishi, ZnSe crystal growth by radical assisted MOCVD 100/101 (1996) 621
- Hatanaka, Y., see Nakanishi, Y. 100/101 (1996) 639
- Hatano, T., see Suehara, S. 100/101 (1996) 252
- Hatta, A., see Wadayama, T. 100/101 (1996) 575
- Hattori, M., S. Sekine, T. Ooie and H. Nonaka, Time-resolved detection of laser-ablated particles based on intensity decrease of cw probe laser beam 100/101 (1996) 301
- Hattori, T., see Yamauchi, S. 100/101 (1996) 522
- Hayashi, K., see Iwano, H. 100/101 (1996) 487
- Hayashi, N., see Kobayashi, N. 100/101 (1996) 498
- Heck, C., see Jikimoto, T. 100/101 (1996) 513
- Hems, J., see Sykes, D.E. 100/101 (1996) 77
- Heyn, Ch. and M. Harsdorff, Routine measurement of the absolute As₄ flux in a molecular beam epitaxy system with conventional RHEED equipment 100/101 (1996) 494
- Hirai, M., see Jikimoto, T. 100/101 (1996) 513
- Hirai, M., see Yamauchi, S. 100/101 (1996) 522
- Hiraki, A., see Tachiwaki, T. 100/101 (1996) 272
- Hirano, S., see Gheyas, S.I. 100/101 (1996) 634
- Hirano, S., see Gheyas, S.I. 100/101 (1996) 647
- Hiraoka, A., see Yano, F. 100/101 (1996) 138
- Hirayama, H., K. Watanabe and M. Kawada, Doping dependence of second harmonic generation from native oxide/Si(111) interfaces 100/101 (1996) 460
- Hishita, S., see Oyoshi, K. 100/101 (1996) 374
- Holloway, P.H., see Viljoen, P.E. 100/101 (1996) 612
- Homma, T., see Suzuki, Y. 100/101 (1996) 165
- Homma, T., M. Minato, Y. Itoh, S. Akiya and T. Suzuki, A modified surface of titanium and its vacuum characteristic 100/101 (1996) 189
- Hong, C.-S., see Chen, B.-Y. 100/101 (1996) 601
- Horio, Y., Y. Hashimoto and A. Ichimiya, A new type of RHEED apparatus equipped with an energy filter 100/101 (1996) 292
- Horiuchi, T., see Ishida, K. 100/101 (1996) 116
- Hoshi, T., see Morohashi, T. 100/101 (1996) 84
- Hoshi, T., see Kudo, M. 100/101 (1996) 129
- Hosokawa, N., see Numajiri, K. 100/101 (1996) 541
- Hosokawa, N., see Kim, S.W. 100/101 (1996) 546
- Hotta, K., see Ikeda, H. 100/101 (1996) 431
- Hsu, C.C., see Chen, W.D. 100/101 (1996) 530
- Ichiki, K., see Hatakeyama, M. 100/101 (1996) 277
- Ichimiya, A., see Horio, Y. 100/101 (1996) 292
- Ichimiya, A., see Emoto, T. 100/101 (1996) 355
- Ichimura, S., see Tanuma, S. 100/101 (1996) 47
- Ichimura, S., see Kurokawa, A. 100/101 (1996) 436
- Ichimura, S., see Nakamura, K. 100/101 (1996) 444
- Ichino, K., see Lee, S.T. 100/101 (1996) 656
- Idota, K., M. Niwa and I. Sumita, Ultrahigh vacuum system for atomic-scale planarization of 6 inch Si(001) substrate 100/101 (1996) 311
- Iida, M., see Ying, W.B. 100/101 (1996) 556

- Iida, M., see Mizokawa, Y. 100/101 (1996) 561
- Iijima, M., M. Sato and Y. Takahashi, Photoresist characteristics of polyurea films prepared by vapor deposition polymerization. Depolymerization of polyurea 100/101 (1996) 120
- Ikeda, H., T. Yamada, K. Hotta, S. Zaima and Y. Yasuda, Initial oxidation of Si(311) surfaces studied by high-resolution electron energy loss spectroscopy 100/101 (1996) 431
- Ikeda, H., see Shinoda, H. 100/101 (1996) 526
- Ikeo, N., see Sekine, T. 100/101 (1996) 30
- Imada, H., see Tumiran, 100/101 (1996) 238
- Imamura, M., see Shimada, H. 100/101 (1996) 56
- Inanaga, K., T. Nakahata, T. Furukawa and K. Ono, Initial stage of oxidation of Si(100) surfaces in dry oxygen 100/101 (1996) 421
- Inoue, K., see Mitsui, T. 100/101 (1996) 625
- Ishida, K., T. Horiuchi, S. Kai and K. Matsushige, Structural properties of epitaxially grown perfluoro *n*-alkane thin films prepared by vapor deposition 100/101 (1996) 116
- Ishihara, M., see Saito, S. 100/101 (1996) 260
- Ishijima, A., see Kudo, M. 100/101 (1996) 134
- Ishikawa, J., see Tsuji, H. 100/101 (1996) 342
- Ishikawa, J., see Toyota, Y. 100/101 (1996) 360
- Ishikawa, J., H. Tsuji, K. Kameyama, S. Shimada and Y. Gotoh, Development of ion irradiation system for in situ observation of ion irradiated semiconductor surfaces by ultra high vacuum scanning tunneling microscope 100/101 (1996) 370
- Ishikawa, T., see Yoshida, S. 100/101 (1996) 184
- Ito, H., M. Ito, Y. Magatani and F. Soeda, Submicron particle analysis by the Auger microprobe (FE-SAM) 100/101 (1996) 152
- Ito, M., see Ito, H. 100/101 (1996) 152
- Ito, T., see Tachiwaki, T. 100/101 (1996) 272
- Itoga, T., see Yano, F. 100/101 (1996) 138
- Itoh, H., see Tsuji, H. 100/101 (1996) 342
- Itoh, N., see Szymonski, M. 100/101 (1996) 102
- Itoh, Y., see Suzuki, Y. 100/101 (1996) 165
- Itoh, Y., see Homma, T. 100/101 (1996) 189
- Iwai, H., R. Oiwa, P.E. Larson and M. Kudo, Simulation of geometrical aberration and beam shape of scanning X-ray probe 100/101 (1996) 283
- Iwaki, M., see Nakao, A. 100/101 (1996) 112
- Iwami, M., see Jikimoto, T. 100/101 (1996) 513
- Iwami, M., see Yamauchi, S. 100/101 (1996) 522
- Iwano, H., K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda, Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on Si(100) by MBE 100/101 (1996) 487
- Iwasawa, Y., see Chun, W.-J. 100/101 (1996) 143
- Iwaso, M. and T. Arakawa, Luminescent properties of an anodically oxidized P-doped silicon wafer 100/101 (1996) 147
- Izumi, Y., M. Katoh, T. Ohte, S. Ohtani, A. Kojima and N. Saitoh, Heating effects on modifying carbon surface by reactive plasma 100/101 (1996) 179
- Izumi, Y., see Katoh, M. 100/101 (1996) 226
- Jablonski, A., see Tilinin, I.S. 100/101 (1996) 20
- Jennett, N.M., see Meneve, J.L. 100/101 (1996) 64
- Jenq, F.-L., see Chen, B.-Y. 100/101 (1996) 601
- Jeong, C.S., see Lee, J.C. 100/101 (1996) 97
- Jikimoto, T., C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami, Co overlayer formation process on Si(100) 2×1 studied by SR-PES 100/101 (1996) 513
- Jimba, H., see Kim, S.W. 100/101 (1996) 546
- Jimbo, T., see Uchida, H. 100/101 (1996) 399
- Jimbo, T., see Hasegawa, Y. 100/101 (1996) 482
- Jimbo, T., see Yu, G. 100/101 (1996) 617
- Jo, M. and A. Tanaka, Auger electron peaks of Cu in XPS 100/101 (1996) 11
- Kai, S., see Ishida, K. 100/101 (1996) 116
- Kaibara, M., see Nakao, A. 100/101 (1996) 112
- Kameyama, K., see Ishikawa, J. 100/101 (1996) 370
- Kamidoi, S., see Kawano, H. 100/101 (1996) 174
- Kamiura, Y., see Ying, W.B. 100/101 (1996) 556
- Kamiura, Y., see Mizokawa, Y. 100/101 (1996) 561
- Kanehori, K., see Yano, F. 100/101 (1996) 138
- Kang, H.J., see Lee, J.C. 100/101 (1996) 97
- Kang, H.J., C.H. Kim, N.S. Park and M.W. Kim, The surface and interface reaction of metal thin film on sapphire substrate 100/101 (1996) 160
- Kang, H.J., C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald, Preferential sputtering and surface segregation of CuZr alloys 100/101 (1996) 329
- Kato, H., see Takemura, S. 100/101 (1996) 107
- Katoh, M., see Izumi, Y. 100/101 (1996) 179
- Katoh, M., Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani, Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis 100/101 (1996) 226
- Katsumata, H., see Kobayashi, N. 100/101 (1996) 498
- Kawada, H., S. Reiff and J.H. Block, CHF_3 adsorption and decomposition on clean and oxygen covered Al(111) 100/101 (1996) 587
- Kawada, M., see Hirayama, H. 100/101 (1996) 460
- Kawaguchi, K., see Pindoria, G. 100/101 (1996) 347
- Kawamoto, K., see Ying, W.B. 100/101 (1996) 556
- Kawamoto, K., see Mizokawa, Y. 100/101 (1996) 561
- Kawano, H., S. Kamidoi, H. Shimizu, K. Ushimaru and H. Asada, Temperature-programmed desorption of positive ions and neutral molecules from alkali halide layers deposited on a metal surface 100/101 (1996) 174

- Kawano, H., K. Ohgami, S. Matsui and Y. Kitayama, Empirical formulae of the threshold temperature range for dissociative positive ionization of alkali halides on heated metal surfaces 100/101 (1996) 193
- Kawano, H., K. Ohgami and N. Serizawa, Thermal positive ion production from thallium chloride molecules impinging upon a tungsten surface heated in high vacua 100/101 (1996) 199
- Kawata, J. and K. Ohya, Monte Carlo simulation of ion-induced kinetic electron emission from a metal surface 100/101 (1996) 338
- Keim, E., see Futamata, M. 100/101 (1996) 60
- Kim, C.H., see Kang, H.J. 100/101 (1996) 160
- Kim, C.H., see Kang, H.J. 100/101 (1996) 329
- Kim, H.K., see Lee, J.C. 100/101 (1996) 97
- Kim, M.W., see Kang, H.J. 100/101 (1996) 160
- Kim, S.W., H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa, Low pressure MOCVD of TiN thin films 100/101 (1996) 546
- Kimura, H., see Katoh, M. 100/101 (1996) 226
- King, D.A., see Mitrelias, T. 100/101 (1996) 305
- Kita, A., M. Ozawa and C.D. Gutleben, XPS analysis of chemically etched II-VI semiconductor surfaces 100/101 (1996) 652
- Kitada, T., T. Harada and S. Tanuma, Analysis of Auger sputter depth profiles with a resolution function 100/101 (1996) 89
- Kitagawa, M., see Lee, S.T. 100/101 (1996) 656
- Kitagawa, Y., see Takemura, S. 100/101 (1996) 107
- Kitayama, Y., see Kawano, H. 100/101 (1996) 193
- Kobayashi, H., see Lee, S.T. 100/101 (1996) 656
- Kobayashi, N., see Makimoto, T. 100/101 (1996) 403
- Kobayashi, N., see Uwai, K. 100/101 (1996) 412
- Kobayashi, N., M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa, Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization 100/101 (1996) 498
- Kobayashi, S., see Tumiran, 100/101 (1996) 238
- Kobayashi, Y. and T. Ogino, Infrared external reflection spectroscopy of self-assembled monolayer films on Si substrate with a buried metal layer (BML) structure 100/101 (1996) 407
- Köhler, K., Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters 100/101 (1996) 383
- Kojima, A., see Izumi, Y. 100/101 (1996) 179
- Kojima, A., see Katoh, M. 100/101 (1996) 226
- Kojima, A., see Iwano, H. 100/101 (1996) 487
- Kojima, H., see Yano, F. 100/101 (1996) 138
- Kojima, J., see Shinoda, H. 100/101 (1996) 526
- Kolodziej, J., see Szymonski, M. 100/101 (1996) 102
- Komatsu, K., see Emoto, T. 100/101 (1996) 355
- Komiya, S., see Sugita, Y. 100/101 (1996) 268
- Komoku, K., see Jikimoto, T. 100/101 (1996) 513
- Konishi, R., see Yea, B. 100/101 (1996) 365
- Kore-eda, T., see Takeuchi, T. 100/101 (1996) 596
- Korecki, P., see Szymonski, M. 100/101 (1996) 102
- Kosaka, M., see Shinoda, H. 100/101 (1996) 526
- Koshizuka, N., see Saito, S. 100/101 (1996) 260
- Kudo, M., see Morohashi, T. 100/101 (1996) 84
- Kudo, M., S. Yamada, S. Yoshida, T. Watanabe and T. Hoshi, Secondary ion emission from Langmuir-Blodgett (LB) films investigated by time-of-flight secondary ion mass spectrometry 100/101 (1996) 129
- Kudo, M., A. Ishijima and T. Morohashi, Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy 100/101 (1996) 134
- Kudo, M., see Iwai, H. 100/101 (1996) 283
- Kudo, M., see Yamada, T. 100/101 (1996) 287
- Kure, T., see Ninomiya, K. 100/101 (1996) 551
- Kuroda, K., see Ninomiya, K. 100/101 (1996) 551
- Kurokawa, A. and S. Ichimura, High purity ozone oxidation on hydrogen passivated silicon surface 100/101 (1996) 436
- Kusaka, M., see Jikimoto, T. 100/101 (1996) 513
- Kusaka, M., see Yamauchi, S. 100/101 (1996) 522
- Kusakabe, M., see Nakao, A. 100/101 (1996) 112
- Kusunoki, T. and M. Suzuki, Quantitative relationship between the work function and transfer ratio of a potassium-adsorbed MIM cathode 100/101 (1996) 207
- Kuwabara, H., see Nakanishi, Y. 100/101 (1996) 639
- Larson, P.E., see Iwai, H. 100/101 (1996) 283
- Lee, J.C., C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon, Damage profiling of Ar⁺ sputtered Si(100) surface by medium energy ion scattering spectroscopy 100/101 (1996) 97
- Lee, S.T., M. Kitagawa, K. Ichino and H. Kobayashi, Preparation and photoluminescent characteristics of Zn_xSr_{1-x}S:Ce thin films 100/101 (1996) 656
- Lesiak-Orlowska, B., see Tilinin, I.S. 100/101 (1996) 20
- Li, X., see Zhou, B. 100/101 (1996) 643
- Li, X.Q., see Chen, W.D. 100/101 (1996) 592
- Lioubtchenko, D.V., see Bryantseva, T.A. 100/101 (1996) 169
- Lopatin, V.V., see Bryantseva, T.A. 100/101 (1996) 169
- MacDonald, R., see Kang, H.J. 100/101 (1996) 329
- Maciel, H.S., see Mansano, R.D. 100/101 (1996) 583
- Maeda, T., see Saito, S. 100/101 (1996) 260
- Maeyama, M., see Tumiran, 100/101 (1996) 238
- Magatani, Y., see Ito, H. 100/101 (1996) 152
- Maiwa, Y., see Wadayama, T. 100/101 (1996) 575

- Makimoto, T. and N. Kobayashi, Nitridation of GaAs surfaces using nitrogen molecules cracked by a hot tungsten filament 100/101 (1996) 403
- Makita, Y., see Kobayashi, N. 100/101 (1996) 498
- Mansano, R.D., P. Verdonck and H.S. Maciel, Deep trench etching in silicon with fluorine containing plasmas 100/101 (1996) 583
- Maquin, Ph., see Puech, M. 100/101 (1996) 579
- Margail, J., see Regolini, J.L. 100/101 (1996) 566
- Matsubayashi, N., see Shimada, H. 100/101 (1996) 56
- Matsui, S., see Kawano, H. 100/101 (1996) 193
- Matsuo, Y. and K. Oishi, Oxide thickness dependence of photocurrent for the GeO_2/Ge film system 100/101 (1996) 248
- Matsushige, K., see Ishida, K. 100/101 (1996) 116
- Maury, D., see Regolini, J.L. 100/101 (1996) 566
- Meneve, J.L., J.F. Smith, N.M. Jennett and S.R.J. Saunders, Surface mechanical property testing by depth sensing indentation 100/101 (1996) 64
- Mikado, T., see Ohdaira, T. 100/101 (1996) 73
- Mikado, T., see Suzuki, R. 100/101 (1996) 297
- Minato, M., see Suzuki, Y. 100/101 (1996) 165
- Minato, M., see Homma, T. 100/101 (1996) 189
- Minemura, J., see Uchida, Y. 100/101 (1996) 478
- Mitrelias, T., V.P. Ostanin, M. Gruyters and D.A. King, Design of an ultrahigh vacuum compatible system for studying the influence of acoustic waves on surface chemical processes 100/101 (1996) 305
- Mitsui, T., N. Yamamoto, J. Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue, Correlation between cathodoluminescence and structural defects in $\text{ZnS}/\text{GaAs}(100)$ and $\text{ZnSe}/\text{GaAs}(100)$ studied by transmission electron microscopy 100/101 (1996) 625
- Mitsui, Y., see Yano, F. 100/101 (1996) 138
- Miura, T., M. Niwano, D. Shoji and N. Miyamoto, Initial stages of oxidation of hydrogen-terminated Si surface stored in air 100/101 (1996) 454
- Miura, T., see Niwano, M. 100/101 (1996) 607
- Miyamoto, N., see Enta, Y. 100/101 (1996) 449
- Miyamoto, N., see Miura, T. 100/101 (1996) 454
- Miyamoto, N., see Niwano, M. 100/101 (1996) 607
- Mizokawa, Y., see Ying, W.B. 100/101 (1996) 556
- Mizokawa, Y., W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto, Phosphorus redistribution in the surface region of heavily phosphorus doped silicon 100/101 (1996) 561
- Mogi, K., see Suzuki, M. 100/101 (1996) 51
- Moon, D.W., see Lee, J.C. 100/101 (1996) 97
- Morin, C., see Regolini, J.L. 100/101 (1996) 566
- Morishita, T., see Pindoria, G. 100/101 (1996) 347
- Morita, M., see Hatanaka, Y. 100/101 (1996) 621
- Morita, Y. and H. Tokumoto, STM analysis of wet-chemically prepared H-Si(001) surface 100/101 (1996) 440
- Morohashi, T., T. Hoshi, H. Nikaido and M. Kudo, Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis 100/101 (1996) 84
- Morohashi, T., see Kudo, M. 100/101 (1996) 134
- Morokawa, S., see Sakamoto, K. 100/101 (1996) 124
- Tumiran, S., Kobayashi, M. Maeyama, H. Imada and Y. Saito, The correlation between surface charge distribution and flashover properties of alumina surface in vacuum 100/101 (1996) 238
- Mu, C., see Numajiri, K. 100/101 (1996) 541
- Murata, J., T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda, Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS and RHEED 100/101 (1996) 417
- Nagahama, I., see Hatakeyama, M. 100/101 (1996) 277
- Nagasawa, Y., see Sekine, T. 100/101 (1996) 30
- Nagumo, S., see Toyota, Y. 100/101 (1996) 360
- Nakahata, T., see Inanaga, K. 100/101 (1996) 421
- Nakajima, Y., see Takemura, S. 100/101 (1996) 107
- Nakamura, K., S. Ichimura and H. Shimizu, Oxygen adsorption on hydrogen-preadsorbed $\text{Si}(111)7 \times 7$ observed by second harmonic generation (SHG) 100/101 (1996) 444
- Nakamura, T., see Nakanishi, Y. 100/101 (1996) 639
- Nakane, H., see Satoh, H. 100/101 (1996) 216
- Nakane, H., see Endo, M. 100/101 (1996) 378
- Nakanishi, Y., see Hatanaka, Y. 100/101 (1996) 621
- Nakanishi, Y., F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka, Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4:\text{Ce}$ thin films by multi-source deposition 100/101 (1996) 639
- Nakao, A., M. Kaibara, M. Iwaki, Y. Suzuki and M. Kusakabe, Surface characterization of cell adhesion controlled polymer modified by ion bombardment 100/101 (1996) 112
- Nakao, M., see Hatakeyama, M. 100/101 (1996) 277
- Nakata, R., see Tanaka, K. 100/101 (1996) 264
- Nikaido, H., see Morohashi, T. 100/101 (1996) 84
- Ninomiya, K., T. Kure, Y. Sudo, K. Kuroda and H. Todokoro, A nondestructive analysis technique for residual thin films in deep-submicron contact holes 100/101 (1996) 551
- Ninomiya, S., see Emoto, T. 100/101 (1996) 355
- Nishijima, A., see Shimada, H. 100/101 (1996) 56
- Nishikawa, H., see Uchida, H. 100/101 (1996) 399
- Nishio, M., see Gheys, S.I. 100/101 (1996) 211
- Nishio, M., see Gheys, S.I. 100/101 (1996) 634
- Nishio, M., see Gheys, S.I. 100/101 (1996) 647
- Nishioka, T., see Sumitomo, K. 100/101 (1996) 503

- Niwa, M., see Idota, K. 100/101 (1996) 311
- Niwa, M., K. Okada and R. Sinclair, Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating 100/101 (1996) 425
- Niwano, M., see Miura, T. 100/101 (1996) 454
- Niwano, M., T. Miura, R. Tajima and N. Miyamoto, Infrared study of chemistry of Si surfaces in etching solution 100/101 (1996) 607
- Nonaka, H., see Hattori, M. 100/101 (1996) 301
- Nukui, A., see Suehara, S. 100/101 (1996) 252
- Numajiri, K., T. Goya, R. Tobe, O. Okada, N. Hosokawa, C. Mu, N. Cox, C. Scott and J. Yu, High-rate deposition of high-quality Cu film with LPCVD 100/101 (1996) 541
- O'Connor, D.J., see Kang, H.J. 100/101 (1996) 329
- Ogawa, H., see Gheyas, S.I. 100/101 (1996) 211
- Ogawa, H., see Gheyas, S.I. 100/101 (1996) 634
- Ogawa, H., see Gheyas, S.I. 100/101 (1996) 647
- Ogino, T., see Kobayashi, Y. 100/101 (1996) 407
- Ogino, T., see Sumitomo, K. 100/101 (1996) 503
- Ogino, T., see Prabhakaran, K. 100/101 (1996) 518
- Ohdaira, T., R. Suzuki, T. Mikado, H. Ohgaki, M. Chiwaki, T. Yamazaki and M. Hasegawa, High sensitivity of positron-annihilation induced Auger-electron spectroscopy to surface impurities 100/101 (1996) 73
- Ohdaira, T., see Suzuki, R. 100/101 (1996) 297
- Ohgaki, H., see Ohdaira, T. 100/101 (1996) 73
- Ohgaki, H., see Suzuki, R. 100/101 (1996) 297
- Ohgami, K., see Kawano, H. 100/101 (1996) 193
- Ohgami, K., see Kawano, H. 100/101 (1996) 199
- Ohno, S., see Sakka, Y. 100/101 (1996) 232
- Ohshima, H., see Yamauchi, S. 100/101 (1996) 522
- Ohta, S., see Mitsui, T. 100/101 (1996) 625
- Ohtani, S., see Izumi, Y. 100/101 (1996) 179
- Ohtani, S., see Katoh, M. 100/101 (1996) 226
- Ohte, T., see Izumi, Y. 100/101 (1996) 179
- Ohte, T., see Katoh, M. 100/101 (1996) 226
- Ohya, K., see Kawata, J. 100/101 (1996) 338
- Oishi, K., see Matsuo, Y. 100/101 (1996) 248
- Oiwa, R., see Iwai, H. 100/101 (1996) 283
- Okada, K., see Niwa, M. 100/101 (1996) 425
- Okada, O., see Numajiri, K. 100/101 (1996) 541
- Okada, O., see Kim, S.W. 100/101 (1996) 546
- Okubo, S., see Shibata, N. 100/101 (1996) 69
- Okuyama, F., see Aoyama, T. 100/101 (1996) 351
- Ono, K., see Inanaga, K. 100/101 (1996) 421
- Ooie, T., see Hattori, M. 100/101 (1996) 301
- Osaki, T., see Yea, B. 100/101 (1996) 365
- Ostanin, V.P., see Mitrelias, T. 100/101 (1996) 305
- Otto, A., see Futamata, M. 100/101 (1996) 60
- Oyoshi, K., S. Hishita, K. Wada, S. Suehara and T. Aizawa, Roughness study of ion-irradiated silica glass surface 100/101 (1996) 374
- Ozawa, M., see Kita, A. 100/101 (1996) 652
- Panjan, P., see Zalar, A. 100/101 (1996) 92
- Park, N.S., see Kang, H.J. 100/101 (1996) 160
- Park, N.S., see Kang, H.J. 100/101 (1996) 329
- Piatkowski, P., see Szymonski, M. 100/101 (1996) 102
- Pindoria, G., M. Badaye, F. Wang, K. Kawaguchi and T. Morishita, Investigation of the physical and chemical interaction of a low energy oxygen ion beam with oxide superconducting films 100/101 (1996) 347
- Postawa, Z., see Szymonski, M. 100/101 (1996) 102
- Prabhakaran, K. and T. Ogino, Behavior of ultrathin layers of Co on Si and Ge systems 100/101 (1996) 518
- Puech, M. and Ph. Maquin, Low temperature etching of Si and PR in high density plasmas 100/101 (1996) 579
- Regolini, J.L., J. Margail, S. Bodnar, D. Maury and C. Morin, Selective epitaxial Si based layers and TiSi₂ deposition by integrated chemical vapor deposition 100/101 (1996) 566
- Reiff, S., see Kawada, H. 100/101 (1996) 587
- Richter, W. and J.-T. Zettler, Real-time analysis of III-V-semiconductor epitaxial growth 100/101 (1996) 465
- Rittaporn, I., see Saito, S. 100/101 (1996) 260
- Roos, W.D., see Viljoen, P.E. 100/101 (1996) 612
- Saito, S., M. Ishihara, T. Tani, T. Maeda, N. Watanabe, I. Rittaporn and N. Koshizuka, Surface oxygen and electrical resistance of YBa₂Cu₄O₈ 100/101 (1996) 260
- Saito, Y., see Tumiran, 100/101 (1996) 238
- Saitoh, N., see Izumi, Y. 100/101 (1996) 179
- Sakai, Y., see Yamada, T. 100/101 (1996) 287
- Sakamoto, K., R. Arafune, S. Ushioda, Y. Suzuki and S. Morokawa, Molecular orientation of polyimide films determined by an optical retardation method 100/101 (1996) 124
- Sakka, Y. and S. Ohno, Hydrogen desorption characteristics of composite Co-TiN nanoparticles 100/101 (1996) 232
- Sanada, N., see Murata, J. 100/101 (1996) 417
- Sasaki, M., see Yoshida, S. 100/101 (1996) 184
- Sasaki, T.A., see Yamamoto, H. 100/101 (1996) 333
- Sato, M., see Iijima, M. 100/101 (1996) 120
- Sato, T., see Shimada, H. 100/101 (1996) 56
- Satoh, H., H. Nakane and H. Adachi, Behavior of zirconium on ZrO/W(100) surface 100/101 (1996) 216
- Saunders, S.R.J., see Meneve, J.L. 100/101 (1996) 64
- Schumacher, D., see Futamata, M. 100/101 (1996) 60
- Scott, C., see Numajiri, K. 100/101 (1996) 541
- Seibt, E.W., see Zalar, A. 100/101 (1996) 92
- Sekiguchi, A., see Kim, S.W. 100/101 (1996) 546
- Sekiguchi, M., see Emoto, T. 100/101 (1996) 355

- Sekine, S., see Hattori, M. 100/101 (1996) 301
- Sekine, T., N. Ikeo and Y. Nagasawa, Comparison of AES chemical shifts with XPS chemical shifts 100/101 (1996) 30
- Sekine, T., see Yamada, T. 100/101 (1996) 287
- Serizawa, N., see Kawano, H. 100/101 (1996) 199
- Shiba, F., see Nakanishi, Y. 100/101 (1996) 639
- Shibata, H., see Kobayashi, N. 100/101 (1996) 498
- Shibata, H., see Wadayama, T. 100/101 (1996) 575
- Shibata, N., S. Okubo and K. Yonemitsu, Depth-dependent non-destructive analysis of thin overlayers using total-reflection-angle X-ray spectroscopy 100/101 (1996) 69
- Shimada, H., N. Matsubayashi, M. Imamura, T. Sato and A. Nishijima, XPS depth profiling by changing incident X-ray energy 100/101 (1996) 56
- Shimada, S., see Ishikawa, J. 100/101 (1996) 370
- Shimizu, H., see Kawano, H. 100/101 (1996) 174
- Shimizu, H., see Nakamura, K. 100/101 (1996) 444
- Shimizu, R., see Ding, Z.-J. 100/101 (1996) 15
- Shinoda, H., M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda, Electrical properties of metal/ $\text{Si}_{1-x}\text{Ge}_x/\text{Si}(100)$ heterojunctions 100/101 (1996) 526
- Shirai, N., see Tanaka, K. 100/101 (1996) 264
- Shoji, D., see Miura, T. 100/101 (1996) 454
- Sinclair, R., see Niwa, M. 100/101 (1996) 425
- Smith, J.F., see Meneve, J.L. 100/101 (1996) 64
- Soeda, F., see Ito, H. 100/101 (1996) 152
- Soga, M., see Furuya, M. 100/101 (1996) 508
- Soga, T., see Yu, G. 100/101 (1996) 617
- Somers, M.A.J., see Graat, P.C.J. 100/101 (1996) 36
- Sowa, K., see Nakanishi, Y. 100/101 (1996) 639
- Stribley, K., see Sykes, D.E. 100/101 (1996) 77
- Sudo, Y., see Ninomiya, K. 100/101 (1996) 551
- Suehara, S., T. Hatano and A. Nukui, Water vapor effects on the TeO_2/Te thin film conductance 100/101 (1996) 252
- Suehara, S., see Oyoshi, K. 100/101 (1996) 374
- Suemitsu, M., see Enta, Y. 100/101 (1996) 449
- Sugahara, K., see Yea, B. 100/101 (1996) 365
- Sugimoto, J., see Tachiwaki, T. 100/101 (1996) 272
- Sugita, Y., S. Watanabe, N. Awaji and S. Komiya, Structural fluctuation of SiO_2 network at the interface with Si 100/101 (1996) 268
- Sumita, I., see Idota, K. 100/101 (1996) 311
- Sumitomo, K., T. Nishioka and T. Ogino, Atomic structure analysis of the interfaces in Si/Ge superlattices 100/101 (1996) 503
- Suntola, T., Surface chemistry of materials deposition at atomic layer level 100/101 (1996) 391
- Suzuki, M., K. Mogi and H. Takenaka, Auger electron spectroscopy measurement of electron attenuation lengths using multilayer systems 100/101 (1996) 51
- Suzuki, M., see Kusunoki, T. 100/101 (1996) 207
- Suzuki, R., see Ohdaira, T. 100/101 (1996) 73
- Suzuki, R., T. Ohdaira, T. Mikado, H. Ohgaki, M. Chiwaki and T. Yamazaki, Apparatus for positron-annihilation-induced Auger electron spectroscopy with a pulsed positron beam 100/101 (1996) 297
- Suzuki, T., see Homma, T. 100/101 (1996) 189
- Suzuki, Y., see Nakao, A. 100/101 (1996) 112
- Suzuki, Y., see Sakamoto, K. 100/101 (1996) 124
- Suzuki, Y., T. Homma, M. Minato and Y. Itoh, Effect of different surface treatments on the precipitation of boron nitride for stainless steel SUS304 100/101 (1996) 165
- Suzuki, Y., see Murata, J. 100/101 (1996) 417
- Swart, H.C., see Viljoen, P.E. 100/101 (1996) 612
- Sykes, D.E., A. Chew, J. Hems and K. Stribley, High depth resolution depth profiling of metal films using SIMS and sample rotation 100/101 (1996) 77
- Szymonski, M., J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh, Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides 100/101 (1996) 102
- Tachiwaki, T., J. Sugimoto, T. Ito and A. Hiraki, Characterization of freeze-dried powders prepared by alkoxide route for YBCO superconductors 100/101 (1996) 272
- Tadokoro, T., see Mitsui, T. 100/101 (1996) 625
- Tajima, R., see Niwano, M. 100/101 (1996) 607
- Takahashi, Y., see Iijima, M. 100/101 (1996) 120
- Takano, H., see Furuya, M. 100/101 (1996) 508
- Takegawa, Y., see Enta, Y. 100/101 (1996) 449
- Takeichi, Y., K. Goto and V. Gaidarova, True Auger spectral shapes (standards) 100/101 (1996) 25
- Takemura, S., Y. Kitagawa, H. Kato and Y. Nakajima, UPS studies of conducting polymers: dopant effect on conjugated polymer systems sensitive to conductivity 100/101 (1996) 107
- Takenaka, H., see Suzuki, M. 100/101 (1996) 51
- Takeuchi, T., see Murata, J. 100/101 (1996) 417
- Takeuchi, T., T. Kore-eda and A. Ebina, Surface barriers formation mechanism of the chemically etched $\text{CdTe}(111)$ polar surfaces and gold interfaces 100/101 (1996) 596
- Tanaka, A., see Jo, M. 100/101 (1996) 11
- Tanaka, K., N. Yokota, N. Shirai, Q. Zhuang and R. Nakata, Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of $\text{CdWO}_4(010)$ 100/101 (1996) 264
- Tanemura, M., see Aoyama, T. 100/101 (1996) 351
- Tani, T., see Saito, S. 100/101 (1996) 260
- Tanioka, H., see Yea, B. 100/101 (1996) 365
- Tansley, T.L., see Zhou, B. 100/101 (1996) 643

- Tanuma, S., S. Ichimura and K. Yoshihara, Calculations of 'effective' inelastic mean free paths in solids 100/101 (1996) 47
- Tanuma, S., see Kitada, T. 100/101 (1996) 89
- Tatsuoka, H., see Nakanishi, Y. 100/101 (1996) 639
- Tilinin, I.S., A. Jablonski and B. Lesiak-Orlowska, The influence of elastic scattering on the concentration dependence of the photoelectron line intensity 100/101 (1996) 20
- Tobe, R., see Numajiri, K. 100/101 (1996) 541
- Todokoro, H., see Ninomiya, K. 100/101 (1996) 551
- Tokumoto, H., see Morita, Y. 100/101 (1996) 440
- Tomizuka, H. and A. Ayame, Charge-up and charge compensation on monochromatized X-ray photoelectron spectroscopic measurements of alumina and glass 100/101 (1996) 243
- Tougaard, S., Quantitative XPS: non-destructive analysis of surface nano-structures 100/101 (1996) 1
- Toyota, Y., see Tsuji, H. 100/101 (1996) 342
- Toyota, Y., H. Tsuji, S. Nagumo, Y. Gotoh and J. Ishikawa, Charging phenomenon of insulators in negative-ion implantation 100/101 (1996) 360
- Tsuji, H., J. Ishikawa, H. Itoh, Y. Toyota and Y. Gotoh, Fundamental study on powder-scattering in positive- and negative-ion implantation into powder materials 100/101 (1996) 342
- Tsuji, H., see Toyota, Y. 100/101 (1996) 360
- Tsuji, H., see Ishikawa, J. 100/101 (1996) 370
- Uchida, H., M. Adachi, H. Nishikawa, T. Egawa, T. Jimbo and M. Umeno, CBE-grown high-quality GaAs on Si substrate 100/101 (1996) 399
- Uchida, Y., J. Minemura, Y. Yazawa and T. Warabisako, Epitaxial growth of GaAs on HF-treated Si substrates 100/101 (1996) 478
- Uekusa, S., see Kobayashi, N. 100/101 (1996) 498
- Umeno, M., see Uchida, H. 100/101 (1996) 399
- Umeno, M., see Hasegawa, Y. 100/101 (1996) 482
- Umeno, M., see Yu, G. 100/101 (1996) 617
- Urisu, T., see Gheys, S.I. 100/101 (1996) 211
- Ushimaru, K., see Kawano, H. 100/101 (1996) 174
- Ushioda, S., see Sakamoto, K. 100/101 (1996) 124
- Utsumi, K., see Yoshida, A. 100/101 (1996) 491
- Uwai, K., Y. Yamauchi and N. Kobayashi, In situ observation of nitridation of GaAs (001) surfaces by infrared reflectance spectroscopy 100/101 (1996) 412
- Verdonck, P., see Mansano, R.D. 100/101 (1996) 583
- Viljoen, E.C., see du Plessis, J. 100/101 (1996) 222
- Viljoen, P.E., W.D. Roos, H.C. Swart and P.H. Holloway, Carbon Auger peak shape measurements in the characterization of reactions on (001) diamond 100/101 (1996) 612
- Wada, K., see Oyoshi, K. 100/101 (1996) 374
- Wadayama, T., Y. Maiwa, H. Shibata and A. Hatta, In-situ IR and mass spectroscopic study of the $\text{Al}(\text{CH}_3)_2\text{H}/\text{a-Si:H}$ reaction processes 100/101 (1996) 575
- Wang, F., see Pindoria, G. 100/101 (1996) 347
- Warabisako, T., see Uchida, Y. 100/101 (1996) 478
- Watanabe, K., see Hirayama, H. 100/101 (1996) 460
- Watanabe, N., see Saito, S. 100/101 (1996) 260
- Watanabe, S., see Sugita, Y. 100/101 (1996) 268
- Watanabe, T., see Kudo, M. 100/101 (1996) 129
- Xie, X.L., see Chen, W.D. 100/101 (1996) 530
- Xie, X.L., see Chen, W.D. 100/101 (1996) 592
- Yamada, S., see Kudo, M. 100/101 (1996) 129
- Yamada, T., M. Kudo, Y. Ando, T. Sekine and Y. Sakai, Development of high spatial resolution Auger microscope as applied to semiconductor analysis 100/101 (1996) 287
- Yamada, T., see Ikeda, H. 100/101 (1996) 431
- Yamamoto, H., Y. Baba and T.A. Sasaki, Dissociative scattering of low-energy SiF_3^+ and SiF^+ ions (5–200 eV) on Cu(100) surface 100/101 (1996) 333
- Yamamoto, N., see Mitsui, T. 100/101 (1996) 625
- Yamauchi, S., Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami, Valence band structure of metal silicides modified by argon ion implantation 100/101 (1996) 522
- Yamauchi, Y., see Uwai, K. 100/101 (1996) 412
- Yamazaki, T., see Ohdaira, T. 100/101 (1996) 73
- Yamazaki, T., see Suzuki, R. 100/101 (1996) 297
- Yanagisawa, Y., NO interaction with thermally activated CaO and SrO surfaces 100/101 (1996) 256
- Yanashima, K., see Mitsui, T. 100/101 (1996) 625
- Yano, F., A. Hiraoka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui, Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere 100/101 (1996) 138
- Yasuda, Y., see Ikeda, H. 100/101 (1996) 431
- Yasuda, Y., see Iwano, H. 100/101 (1996) 487
- Yasuda, Y., see Shinoda, H. 100/101 (1996) 526
- Yazawa, Y., see Uchida, Y. 100/101 (1996) 478
- Yea, B., R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara, Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere 100/101 (1996) 365
- Ying, W.B., Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto, Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon 100/101 (1996) 556

- | | | | |
|--|--------------------|---|--------------------|
| Ying, W.B., see Mizokawa, Y. | 100/101 (1996) 561 | GaAs on Si by spectroscopic ellipsometry | 100/101 (1996) 617 |
| Yokota, N., see Tanaka, K. | 100/101 (1996) 264 | Yu, J., see Numajiri, K. | 100/101 (1996) 541 |
| Yonemitsu, K., see Shibata, N. | 100/101 (1996) 69 | Yu, Y.B., see Ying, W.B. | 100/101 (1996) 556 |
| Yoshida, A., K. Utsumi and A. Ganjoo, Si epitaxial growth at low temperatures using remote plasma process | 100/101 (1996) 491 | Yu, Y.B., see Mizokawa, Y. | 100/101 (1996) 561 |
| Yoshida, S., see Kudo, M. | 100/101 (1996) 129 | | |
| Yoshida, S., M. Sasaki and T. Ishikawa, The effect of EB irradiation with and without hot-jet Cl ₂ on an ultra-thin GaN layer for selective etching | 100/101 (1996) 184 | Zaima, S., see Ikeda, H. | 100/101 (1996) 431 |
| Yoshihara, K., see Tanuma, S. | 100/101 (1996) 47 | Zaima, S., see Iwano, H. | 100/101 (1996) 487 |
| Yoshihara, K., see Yoshitake, M. | 100/101 (1996) 203 | Zaima, S., see Shinoda, H. | 100/101 (1996) 526 |
| Yoshikawa, K., see Iwano, H. | 100/101 (1996) 487 | Zalar, A., E.W. Seibt and P. Panjan, Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions | 100/101 (1996) 92 |
| Yoshino, J., see Mitsui, T. | 100/101 (1996) 625 | Zettler, J.-T., see Richter, W. | 100/101 (1996) 465 |
| Yoshitake, M. and K. Yoshihara, Effect of gas adsorption on the segregation behavior of substrate Cu on Ti film | 100/101 (1996) 203 | Zhou, B., X. Li, T.L. Tansley and K.S.A. Butcher, Microwave plasma assisted LCVD growth and characterization of GaN | 100/101 (1996) 643 |
| Yu, G., T. Soga, T. Jimbo and M. Umeno, Characterization of MOCVD-grown | | Zhuang, Q., see Tanaka, K. | 100/101 (1996) 264 |



ELSEVIER

Applied Surface Science 100/101 (1996) 669-689

applied
surface science

Subject index

Ablation

- Time-resolved detection of laser-ablated particles based on intensity decrease of cw probe laser beam, M. Hattori, S. Sekine, T. Ooie and H. Nonaka 100/101 (1996) 301

Acoustic effects

- Design of an ultrahigh vacuum compatible system for studying the influence of acoustic waves on surface chemical processes, T. Mitrelias, V.P. Ostanin, M. Gruyters and D.A. King 100/101 (1996) 305

Alkali halides

- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- Temperature-programmed desorption of positive ions and neutral molecules from alkali halide layers deposited on a metal surface, H. Kawano, S. Kamidoi, H. Shimizu, K. Ushimaru and H. Asada 100/101 (1996) 174
- Empirical formulae of the threshold temperature range for dissociative positive ionization of alkali halides on heated metal surfaces, H. Kawano, K. Ohgami, S. Matsui and Y. Kitayama 100/101 (1996) 193

Alkali metals

- Quantitative relationship between the work function and transfer ratio of a potassium-adsorbed MIM cathode, T. Kusonoki and M. Suzuki 100/101 (1996) 207

Alloys

- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H.

- Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329

- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498

Aluminium

- Determination of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ Auger sensitivity factors, W.D. Chen and Y.D. Cui 100/101 (1996) 156
- Molecular beam epitaxy of $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{In}_y\text{Ga}_{1-y}\text{As}$ heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- In-situ IR and mass spectroscopic study of the $\text{Al}(\text{CH}_3)_2\text{H}/\text{a-Si:H}$ reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575
- CHF_3 adsorption and decomposition on clean and oxygen covered Al(111), H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634

Aluminium oxide

- Surface structure analysis of dispersed metal sites on single crystal metal oxides by means of polarization-dependent total-reflection fluorescent EXAFS, W.-J. Chun, K. Asakura and Y. Iwasawa 100/101 (1996) 143
- The surface and interface reaction of metal thin film on sapphire substrate, H.J.

- Kang, C.H. Kim, N.S. Park and M.W. Kim 100/101 (1996) 160
- The correlation between surface charge distribution and flashover properties of alumina surface in vacuum, Tumiran, S. Kobayashi, M. Maeyama, H. Imada and Y. Saito 100/101 (1996) 238
- Charge-up and charge compensation on monochromatized X-ray photoelectron spectroscopic measurements of alumina and glass, H. Tomizuka and A. Ayame 100/101 (1996) 243

Annealing

- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556
- Photoluminescence enhancement of $(\text{NH}_4)_2\text{S}_x$ passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592

Argon

- Damage profiling of Ar^+ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Angular distribution of particles sputtered from GaAs by Ar^+ and Xe^+ ion bombardment, T. Aoyama, M. Tanemura and F. Okuyama 100/101 (1996) 351
- Valence band structure of metal silicides modified by argon ion implantation, S. Yamauchi, Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 522

Atomic force microscopy

- Investigation of the physical and chemical interaction of a low energy oxygen ion beam with oxide superconducting films, G. Pindoria, M. Badaye, F. Wang, K. Kawaguchi and T. Morishita 100/101 (1996) 347

- Roughness study of ion-irradiated silica glass surface, K. Oyoshi, S. Hishita, K. Wada, S. Suehara and T. Aizawa 100/101 (1996) 374
- CBE-grown high-quality GaAs on Si substrate, H. Uchida, M. Adachi, H. Nishikawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 399
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596

Auger electron spectroscopy

- Auger electron peaks of Cu in XPS, M. Jo and A. Tanaka 100/101 (1996) 11
- Intrinsic Auger signal profiles derived by Monte Carlo analysis, Z.-J. Ding, R. Shimizu and K. Goto 100/101 (1996) 15
- True Auger spectral shapes (standards), Y. Takeichi, K. Goto and V. Gaidarova 100/101 (1996) 25
- Comparison of AES chemical shifts with XPS chemical shifts, T. Sekine, N. Ikeo and Y. Nagasawa 100/101 (1996) 30
- A general procedure for extracting quantitative depth information from take-off-angle-resolved XPS and AES, W.H. Gries 100/101 (1996) 41
- Auger electron spectroscopy measurement of electron attenuation lengths using multilayer systems, M. Suzuki, K. Mogi and H. Takenaka 100/101 (1996) 51
- High sensitivity of positron-annihilation induced Auger-electron spectroscopy to surface impurities, T. Ohdaira, R. Suzuki, T. Mikado, H. Ohgaki, M. Chiwaki, T. Yamazaki and M. Hasegawa 100/101 (1996) 73
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Analysis of Auger sputter depth profiles with a resolution function, T. Kitada, T. Harada and S. Tanuma 100/101 (1996) 89
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92
- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron

- spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Submicron particle analysis by the Auger microprobe (FE-SAM), H. Ito, M. Ito, Y. Magatani and F. Soeda 100/101 (1996) 152
- Determination of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ Auger sensitivity factors, W.D. Chen and Y.D. Cui 100/101 (1996) 156
- Ga migration process in Au film on (100) GaAs under temperature treatment in vacuum, T.A. Bryantseva, D.V. Lioubtchenko and V.V. Lopatin 100/101 (1996) 169
- The effect of EB irradiation with and without hot-jet Cl_2 on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184
- Effect of gas adsorption on the segregation behavior of substrate Cu on Ti film, M. Yoshitake and K. Yoshihara 100/101 (1996) 203
- Sn segregation to the low index surfaces of a copper single crystal, J. du Plessis and E.C. Viljoen 100/101 (1996) 222
- Development of high spatial resolution Auger microscope as applied to semiconductor analysis, T. Yamada, M. Kudo, Y. Ando, T. Sekine and Y. Sakai 100/101 (1996) 287
- Apparatus for positron-annihilation-induced Auger electron spectroscopy with a pulsed positron beam, R. Suzuki, T. Ohdaira, T. Mikado, H. Ohgaki, M. Chiwaki and T. Yamazaki 100/101 (1996) 297
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Field emission from transition metal nitride, M. Endo, H. Nakane and H. Adachi 100/101 (1996) 378
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- CHF_3 adsorption and decomposition on clean and oxygen covered Al(111), H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587
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- Carbon Auger peak shape measurements in the characterization of reactions on (001) diamond, P.E. Viljoen, W.D. Roos, H.C. Swart and P.H. Holloway 100/101 (1996) 612
- Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4\text{:Ce}$ thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639
- ### Boron nitride
- Effect of different surface treatments on the precipitation of boron nitride for stainless steel SUS304, Y. Suzuki, T. Homma, M. Minato and Y. Itoh 100/101 (1996) 165
- ### Cadmium
- Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of $\text{CdWO}_4(010)$, K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264
- ### Cadmium telluride
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596
- ### Calcium
- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- ### Carbon
- Heating effects on modifying carbon surface by reactive plasma, Y. Izumi, M. Katoh, T. Ohte, S. Ohtani, A. Kojima and N. Saitoh 100/101 (1996) 179
- Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis, M. Katoh, Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani 100/101 (1996) 226
- ### Cerium
- Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4\text{:Ce}$ thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639

Chemical vapour deposition

- GaAs-based LED on Si substrate with GaAs islands active region by droplet-epitaxy, Y. Hasegawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 482
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- High-rate deposition of high-quality Cu film with LPCVD, K. Numajiri, T. Goya, R. Tobe, O. Okada, N. Hosokawa, C. Mu, N. Cox, C. Scott and J. Yu 100/101 (1996) 541
- Low pressure MOCVD of TiN thin films, S.W. Kim, H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa 100/101 (1996) 546
- Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- In-situ IR and mass spectroscopic study of the $\text{Al}(\text{CH}_3)_2\text{H}/\text{a-Si:H}$ reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634
- Microwave plasma assisted LCVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643

Chromium

- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92

Cobalt

- Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno 100/101 (1996) 232
- Co overlayer formation process on $\text{Si}(100)-2 \times 1$ studied by SR-PES, T. Jikimoto,

C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 513

- Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino 100/101 (1996) 518

Copper

- Effect of gas adsorption on the segregation behavior of substrate Cu on Ti film, M. Yoshitake and K. Yoshihara 100/101 (1996) 203
- Sn segregation to the low index surfaces of a copper single crystal, J. du Plessis and E.C. Viljoen 100/101 (1996) 222
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Dissociative scattering of low-energy SiF_3^+ and SiF^+ ions (5–200 eV) on Cu(100) surface, H. Yamamoto, Y. Baba and T.A. Sasaki 100/101 (1996) 333
- High-rate deposition of high-quality Cu film with LPCVD, K. Numajiri, T. Goya, R. Tobe, O. Okada, N. Hosokawa, C. Mu, N. Cox, C. Scott and J. Yu 100/101 (1996) 541

Depth profiling

- XPS depth profiling by changing incident X-ray energy, H. Shimada, N. Matsubayashi, M. Imamura, T. Sato and A. Nishijima 100/101 (1996) 56
- Depth-dependent non-destructive analysis of thin overlayers using total-reflection-angle X-ray spectroscopy, N. Shibata, S. Okubo and K. Yonemitsu 100/101 (1996) 69
- High depth resolution depth profiling of metal films using SIMS and sample rotation, D.E. Sykes, A. Chew, J. Hems and K. Stribley 100/101 (1996) 77
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Analysis of Auger sputter depth profiles with a resolution function, T. Kitada, T. Harada and S. Tanuma 100/101 (1996) 89
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92
- Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on Si(100) by MBE, H. Iwano,

- K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508

Diamond

- Carbon Auger peak shape measurements in the characterization of reactions on (001) diamond, P.E. Viljoen, W.D. Roos, H.C. Swart and P.H. Holloway 100/101 (1996) 612

Doping effects

- UPS studies of conducting polymers: dopant effect on conjugated polymer systems sensitive to conductivity, S. Takemura, Y. Kitagawa, H. Kato and Y. Nakajima 100/101 (1996) 107
- Doping dependence of second harmonic generation from native oxide/Si(111) interfaces, H. Hirayama, K. Watanabe and M. Kawada 100/101 (1996) 460
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634

Electrical properties

- The correlation between surface charge distribution and flashover properties of alumina surface in vacuum, Tumiran, S. Kobayashi, M. Maeyama, H. Imada and Y. Saito 100/101 (1996) 238
- Water vapor effects on the TeO₂/Te thin film conductance, S. Suehara, T. Hatano and A. Nukui 100/101 (1996) 252
- Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere, B. Yea, R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara 100/101 (1996) 365
- Electrical properties of metal/Si_{1-x}Ge_x/Si(100) heterojunctions, H. Shinoda, M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596
- A theoretical analysis of temperature dependence on hydrogenated amorphous silicon thin-film transistors with the consid-

- eration of resistance of the a-Si:H film layer as a function of temperature, B.-Y. Chen, J.-R. Chen, F.-L. Jenq and C.-S. Hong 100/101 (1996) 601
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621

Electron diffraction

- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- A new type of RHEED apparatus equipped with an energy filter, Y. Horio, Y. Hashimoto and A. Ichimiya 100/101 (1996) 292
- Ultrahigh vacuum system for atomic-scale planarization of 6 inch Si(001) substrate, K. Idota, M. Niwa and I. Sumita 100/101 (1996) 311
- Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Nitridation of GaAs surfaces using nitrogen molecules cracked by a hot tungsten filament, T. Makimoto and N. Kobayashi 100/101 (1996) 403
- In situ observation of nitridation of GaAs (001) surfaces by infrared reflectance spectroscopy, K. Uwai, Y. Yamauchi and N. Kobayashi 100/101 (1996) 412
- Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS and RHEED, J. Murata, T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda 100/101 (1996) 417
- Epitaxial growth of GaAs on HF-treated Si substrates, Y. Uchida, J. Minemura, Y. Yazawa and T. Warabisako 100/101 (1996) 478
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Routine measurement of the absolute As₄ flux in a molecular beam epitaxy system with conventional RHEED equipment, Ch. Heyn and M. Harsdorff 100/101 (1996) 494

Electron emission

- Quantitative relationship between the work function and transfer ratio of a potassium-adsorbed MIM cathode, T. Kusunoki and M. Suzuki 100/101 (1996) 207
- Monte Carlo simulation of ion-induced kinetic electron emission from a metal surface, J. Kawata and K. Ohya 100/101 (1996) 338

Electron energy loss spectroscopy

- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- Initial oxidation of Si(311) surfaces studied by high-resolution electron energy loss spectroscopy, H. Ikeda, T. Yamada, K. Hotta, S. Zaima and Y. Yasuda 100/101 (1996) 431
- CHF₃ adsorption and decomposition on clean and oxygen covered Al(111), H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587

Electron microscopy

- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Effect of different surface treatments on the precipitation of boron nitride for stainless steel SUS304, Y. Suzuki, T. Homma, M. Minato and Y. Itoh 100/101 (1996) 165
- Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis, M. Katoh, Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani 100/101 (1996) 226
- Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno 100/101 (1996) 232
- New-type focused fast atom beam (F-FAB) source and evaluation of emitted beam density distribution, M. Hatakeyama, I. Nagahama, K. Ichiki, M. Nakao and Y. Hatamura 100/101 (1996) 277
- Development of high spatial resolution Auger microscope as applied to semiconductor analysis, T. Yamada, M. Kudo, Y. Ando, T. Sekine and Y. Sakai 100/101 (1996) 287
- Ultrahigh vacuum system for atomic-scale planarization of 6 inch Si(001) substrate, K. Idota, M. Niwa and I. Sumita 100/101 (1996) 311
- Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid

- thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- Low pressure MOCVD of TiN thin films, S.W. Kim, H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa 100/101 (1996) 546
- A nondestructive analysis technique for residual thin films in deep-submicron contact holes, K. Ninomiya, T. Kure, Y. Sudo, K. Kuroda and H. Todokoro 100/101 (1996) 551
- Selective epitaxial Si based layers and TiSi₂ deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- Correlation between cathodoluminescence and structural defects in ZnS/GaAs(100) and ZnSe/GaAs(100) studied by transmission electron microscopy, T. Mitsui, N. Yamamoto, J. Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue 100/101 (1996) 625

Electron stimulated desorption

- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- The effect of EB irradiation with and without hot-jet Cl₂ on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184

Ellipsometry

- Real-time analysis of III-V-semiconductor epitaxial growth, W. Richter and J.-T. Zettler 100/101 (1996) 465
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617

Epitaxy

- Structural properties of epitaxially grown perfluoro *n*-alkane thin films prepared by vapor deposition, K. Ishida, T. Horiuchi, S. Kai and K. Matsushige 100/101 (1996) 116
- Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Surface chemistry of materials deposition at atomic layer level, T. Suntola 100/101 (1996) 391
- CBE-grown high-quality GaAs on Si substrate, H. Uchida, M. Adachi, H.

- Nishikawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 399
- Real-time analysis of III-V-semiconductor epitaxial growth, W. Richter and J.-T. Zettler 100/101 (1996) 465
- Epitaxial growth of GaAs on HF-treated Si substrates, Y. Uchida, J. Minemura, Y. Yazawa and T. Warabisako 100/101 (1996) 478
- GaAs-based LED on Si substrate with GaAs islands active region by droplet-epitaxy, Y. Hasegawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 482
- Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503
- Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634
- Growth of high-quality ZnTe layers by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 647

Etching

- The effect of EB irradiation with and without hot-jet Cl_2 on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184
- New-type focused fast atom beam (F-FAB) source and evaluation of emitted beam density distribution, M. Hatakeyama, I. Nagahama, K. Ichiki, M. Nakao and Y. Hatamura 100/101 (1996) 277
- Low temperature etching of Si and PR in high density plasmas, M. Puech and Ph. Maquin 100/101 (1996) 579

- Deep trench etching in silicon with fluorine containing plasmas, R.D. Mansano, P. Verdonck and H.S. Maciel 100/101 (1996) 583
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596
- Infrared study of chemistry of Si surfaces in etching solution, M. Niwano, T. Miura, R. Tajima and N. Miyamoto 100/101 (1996) 607

Evaporation

- Structural properties of epitaxially grown perfluoro *n*-alkane thin films prepared by vapor deposition, K. Ishida, T. Horiuchi, S. Kai and K. Matsushige 100/101 (1996) 116
- Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4\text{:Ce}$ thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639

Field emission

- Field emission from transition metal nitride, M. Endo, H. Nakane and H. Adachi 100/101 (1996) 378

Gallium

- Ga migration process in Au film on (100) GaAs under temperature treatment in vacuum, T.A. Bryantseva, D.V. Lioubtchenko and V.V. Lopatin 100/101 (1996) 169
- The effect of EB irradiation with and without hot-jet Cl_2 on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184
- Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4\text{:Ce}$ thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639
- Microwave plasma assisted LCVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643

Gallium arsenide

- Analysis of Auger sputter depth profiles with a resolution function, T. Kitada, T. Harada and S. Tanuma 100/101 (1996) 89
- Determination of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ Auger sensitivity factors, W.D. Chen and Y.D. Cui 100/101 (1996) 156

- Ga migration process in Au film on (100) GaAs under temperature treatment in vacuum, T.A. Bryantseva, D.V. Lioubtchenko and V.V. Lopatin 100/101 (1996) 169
- Adsorption and thermal decomposition of diethyltellurium on GaAs(100), S.I. Gheyas, M. Nishio, T. Urisu and H. Ogawa 100/101 (1996) 211
- Angular distribution of particles sputtered from GaAs by Ar⁺ and Xe⁺ ion bombardment, T. Aoyama, M. Tanemura and F. Okuyama 100/101 (1996) 351
- Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- CBE-grown high-quality GaAs on Si substrate, H. Uchida, M. Adachi, H. Nishikawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 399
- Nitridation of GaAs surfaces using nitrogen molecules cracked by a hot tungsten filament, T. Makimoto and N. Kobayashi 100/101 (1996) 403
- In situ observation of nitridation of GaAs (001) surfaces by infrared reflectance spectroscopy, K. Uwai, Y. Yamauchi and N. Kobayashi 100/101 (1996) 412
- Epitaxial growth of GaAs on HF-treated Si substrates, Y. Uchida, J. Minemura, Y. Yazawa and T. Warabisako 100/101 (1996) 478
- GaAs-based LED on Si substrate with GaAs islands active region by droplet-epitaxy, Y. Hasegawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 482
- Routine measurement of the absolute As₄ flux in a molecular beam epitaxy system with conventional RHEED equipment, Ch. Heyn and M. Harsdorff 100/101 (1996) 494
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617
- Correlation between cathodoluminescence and structural defects in ZnS/GaAs(100) and ZnSe/GaAs(100) studied by transmission electron microscopy, T. Mitsui, N. Yamamoto, J. Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue 100/101 (1996) 625
- Gallium phosphide*
- Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS and RHEED, J. Murata, T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda 100/101 (1996) 417
- Germanium*
- Oxide thickness dependence of photocurrent for the GeO₂/Ge film system, Y. Matsuo and K. Oishi 100/101 (1996) 248
- Novel method of strain-relaxed Si_{1-x}Ge_x growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503
- Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino 100/101 (1996) 518
- Electrical properties of metal/Si_{1-x}Ge_x/Si(100) heterojunctions, H. Shinoda, M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526
- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- Glass*
- Charge-up and charge compensation on monochromatized X-ray photoelectron spectroscopic measurements of alumina and glass, H. Tomizuka and A. Ayame 100/101 (1996) 243
- Roughness study of ion-irradiated silica glass surface, K. Oyoshi, S. Hishita, K. Wada, S. Suehara and T. Aizawa 100/101 (1996) 374
- Gold*
- Ga migration process in Au film on (100) GaAs under temperature treatment in vacuum, T.A. Bryantseva, D.V. Lioubtchenko and V.V. Lopatin 100/101 (1996) 169
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596

Halides

- Thermal positive ion production from thallium chloride molecules impinging upon a tungsten surface heated in high vacua, H. Kawano, K. Ohgami and N. Serizawa 100/101 (1996) 199

Hall effect

- Microwave plasma assisted LCVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643

Hydrocarbons

- Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS and RHEED, J. Murata, T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda 100/101 (1996) 417

Hydrogen

- Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno 100/101 (1996) 232
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436
- STM analysis of wet-chemically prepared H-Si(001) surface, Y. Morita and H. Tokumoto 100/101 (1996) 440
- Oxygen adsorption on hydrogen-preadsorbed Si(111)7 × 7 observed by second harmonic generation (SHG), K. Nakamura, S. Ichimura and H. Shimizu 100/101 (1996) 444
- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454
- A theoretical analysis of temperature dependence on hydrogenated amorphous silicon thin-film transistors with the consideration of resistance of the a-Si:H film layer as a function of temperature, B.-Y. Chen, J.-R. Chen, F.-L. Jenq and C.-S. Hong 100/101 (1996) 601

Indium

- Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostruc-

- tures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383

Indium phosphide

- Photoluminescence enhancement of (NH₄)₂S_x passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592

Infrared spectroscopy

- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwaso and T. Arakawa 100/101 (1996) 147
- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Infrared external reflection spectroscopy of self-assembled monolayer films on Si substrate with a buried metal layer (BML) structure, Y. Kobayashi and T. Ogino 100/101 (1996) 407
- In situ observation of nitridation of GaAs (001) surfaces by infrared reflectance spectroscopy, K. Uwai, Y. Yamauchi and N. Kobayashi 100/101 (1996) 412
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454
- In-situ IR and mass spectroscopic study of the Al(CH₃)₂H/a-Si:H reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575
- Infrared study of chemistry of Si surfaces in etching solution, M. Niwano, T. Miura, R. Tajima and N. Miyamoto 100/101 (1996) 607

Interfaces

- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Structural fluctuation of SiO₂ network at the interface with Si, Y. Sugita, S. Watanabe, N. Awaji and S. Komiya 100/101 (1996) 268
- Novel method of strain-relaxed Si_{1-x}Ge_x growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487

- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503

Ion bombardment

- Damage profiling of Ar⁺ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Surface characterization of cell adhesion controlled polymer modified by ion bombardment, A. Nakao, M. Kaibara, M. Iwaki, Y. Suzuki and M. Kusakabe 100/101 (1996) 112
- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Processes in low-energy ion-surface collisions: preferential sputtering, defect and adatom formation, H. Gnaser 100/101 (1996) 316
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Investigation of the physical and chemical interaction of a low energy oxygen ion beam with oxide superconducting films, G. Pindoria, M. Badaye, F. Wang, K. Kawaguchi and T. Morishita 100/101 (1996) 347
- Angular distribution of particles sputtered from GaAs by Ar⁺ and Xe⁺ ion bombardment, T. Aoyama, M. Tanemura and F. Okuyama 100/101 (1996) 351
- Soft X-ray emissions by highly charged ions on solid surfaces: Mo and Ta surfaces, T. Emoto, K. Komatsu, A. Ichimiya, S. Ninomiya and M. Sekiguchi 100/101 (1996) 355
- Development of ion irradiation system for in situ observation of ion irradiated semiconductor surfaces by ultra high vacuum scanning tunneling microscope, J. Ishikawa, H. Tsuji, K. Kameyama, S. Shimada and Y. Gotoh 100/101 (1996) 370
- Roughness study of ion-irradiated silica glass surface, K. Oyoshi, S. Hishita, K. Wada, S. Suehara and T. Aizawa 100/101 (1996) 374

Ion implantation

- Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere, F. Yano, A. Hiraoka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui 100/101 (1996) 138
- Fundamental study on powder-scattering in positive- and negative-ion implantation

- into powder materials, H. Tsuji, J. Ishikawa, H. Itoh, Y. Toyota and Y. Gotoh 100/101 (1996) 342

- Charging phenomenon of insulators in negative-ion implantation, Y. Toyota, H. Tsuji, S. Nagumo, Y. Gotoh and J. Ishikawa 100/101 (1996) 360

- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498

- Valence band structure of metal silicides modified by argon ion implantation, S. Yamauchi, Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 522

Ion scattering

- Damage profiling of Ar⁺ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Dissociative scattering of low-energy SiF₃⁺ and SiF⁺ ions (5–200 eV) on Cu(100) surface, H. Yamamoto, Y. Baba and T.A. Sasaki 100/101 (1996) 333
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503

Iron

- Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra, P.C.J. Graat and M.A.J. Somers 100/101 (1996) 36

Langmuir-Blodgett structures

- Secondary ion emission from Langmuir-Blodgett (LB) films investigated by

- time-of-flight secondary ion mass spectrometry, M. Kudo, S. Yamada, S. Yoshida, T. Watanabe and T. Hoshi 100/101 (1996) 129

Lead

- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134

Low energy electron diffraction

- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
 Sn segregation to the low index surfaces of a copper single crystal, J. du Plessis and E.C. Viljoen 100/101 (1996) 222
 Co overlayer formation process on Si(100)- 2×1 studied by SR-PES, T. Jikimoto, C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 513
 CHF₃ adsorption and decomposition on clean and oxygen covered Al(111), H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587

Luminescence

- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwaso and T. Arakawa 100/101 (1996) 147
 Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of CdWO₄(010), K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264
 Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
 Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
 Photoluminescence enhancement of (NH₄)₂S_x passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592
 Correlation between cathodoluminescence and structural defects in ZnS/GaAs(100) and ZnSe/GaAs(100) studied by transmission electron microscopy, T. Mitsui, N. Yamamoto, J.

- Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue 100/101 (1996) 625
 Aluminum doping of ZnTe grown by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634
 Growth of high-quality ZnTe layers by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 647
 Preparation and photoluminescent characteristics of Zn_xSr_{1-x}S:Ce thin films, S.T. Lee, M. Kitagawa, K. Ichino and H. Kobayashi 100/101 (1996) 656

Mass spectroscopy

- In-situ IR and mass spectroscopic study of the Al(CH₃)₂H/a-Si:H reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575

Methane

- CHF₃ adsorption and decomposition on clean and oxygen covered Al(111), H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587

Molecular beam epitaxy

- Novel method of strain-relaxed Si_{1-x}Ge_x growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
 Routine measurement of the absolute As₄ flux in a molecular beam epitaxy system with conventional RHEED equipment, Ch. Heyn and M. Harsdorff 100/101 (1996) 494
 Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508

Molybdenum

- High sensitivity of positron-annihilation induced Auger-electron spectroscopy to surface impurities, T. Ohdaira, R. Suzuki, T. Mikado, H. Ohgaki, M. Chiwaki, T. Yamazaki and M. Hasegawa 100/101 (1996) 73
 Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
 Soft X-ray emissions by highly charged ions on solid surfaces: Mo and Ta surfaces, T. Emoto, K. Komatsu, A. Ichimiya, S. Ninomiya and M. Sekiguchi 100/101 (1996) 355

Monte Carlo simulations

- Intrinsic Auger signal profiles derived by Monte Carlo analysis, Z.-J. Ding, R. Shimizu and K. Goto 100/101 (1996) 15
- The influence of elastic scattering on the concentration dependence of the photoelectron line intensity, I.S. Tilinin, A. Jablonski and B. Lesiak-Orlowska 100/101 (1996) 20
- Calculations of 'effective' inelastic mean free paths in solids, S. Tanuma, S. Ichimura and K. Yoshihara 100/101 (1996) 47
- Monte Carlo simulation of ion-induced kinetic electron emission from a metal surface, J. Kawata and K. Ohya 100/101 (1996) 338

Multilayers

- Auger electron spectroscopy measurement of electron attenuation lengths using multilayer systems, M. Suzuki, K. Mogi and H. Takenaka 100/101 (1996) 51
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92

Nickel

- True Auger spectral shapes (standards), Y. Takeichi, K. Goto and V. Gaidarova 100/101 (1996) 25
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92

Nitric oxide

- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256

Nitrides

- The effect of EB irradiation with and without hot-jet Cl₂ on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184
- In situ observation of nitridation of GaAs (001) surfaces by infrared reflectance

- spectroscopy, K. Uwai, Y. Yamauchi and N. Kobayashi 100/101 (1996) 412
- Microwave plasma assisted LCVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643

Nitrogen

- Nitridation of GaAs surfaces using nitrogen molecules cracked by a hot tungsten filament, T. Makimoto and N. Kobayashi 100/101 (1996) 403

Optical properties

- Molecular orientation of polyimide films determined by an optical retardation method, K. Sakamoto, R. Arafune, S. Ushioda, Y. Suzuki and S. Morokawa 100/101 (1996) 124
- Oxygen adsorption on hydrogen-preadsorbed Si(111)7 × 7 observed by second harmonic generation (SHG), K. Nakamura, S. Ichimura and H. Shimizu 100/101 (1996) 444
- Doping dependence of second harmonic generation from native oxide/Si(111) interfaces, H. Hirayama, K. Watanabe and M. Kawada 100/101 (1996) 460

Organometallic vapour deposition

- Growth of high-quality ZnTe layers by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 647

Oxidation

- Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere, F. Yano, A. Hiraoka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui 100/101 (1996) 138
- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwaso and T. Arakawa 100/101 (1996) 147
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- Initial oxidation of Si(311) surfaces studied by high-resolution electron energy loss spectroscopy, H. Ikeda, T. Yamada, K. Hotta, S. Zaima and Y. Yasuda 100/101 (1996) 431
- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436

- Growth kinetics of thermal oxidation process on Si(100) by real time ultraviolet photoelectron spectroscopy, Y. Enta, Y. Takegawa, M. Suemitsu and N. Miyamoto 100/101 (1996) 449

- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454

Oxides

- Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra, P.C.J. Graat and M.A.J. Somers 100/101 (1996) 36
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92
- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
- Oxide thickness dependence of photocurrent for the GeO₂/Ge film system, Y. Matsuo and K. Oishi 100/101 (1996) 248
- Water vapor effects on the TeO₂/Te thin film conductance, S. Suehara, T. Hatano and A. Nukui 100/101 (1996) 252
- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of CdWO₄(010), K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264
- Characterization of freeze-dried powders prepared by alkoxide route for YBCO superconductors, T. Tachiwaki, J. Sugimoto, T. Ito and A. Hiraki 100/101 (1996) 272
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556

Oxygen

- Surface oxygen and electrical resistance of YBa₂Cu₄O₈, S. Saito, M. Ishihara, T. Tani, T. Maeda, N. Watanabe, I. Rittaporn and N. Koshizuka 100/101 (1996) 260
- Investigation of the physical and chemical interaction of a low energy oxygen ion beam with oxide superconducting films, G. Pindoria, M. Badaye, F. Wang, K. Kawaguchi and T. Morishita 100/101 (1996) 347

- Oxygen adsorption on hydrogen-preadsorbed Si(111)7 × 7 observed by second harmonic generation (SHG), K. Nakamura, S. Ichimura and H. Shimizu 100/101 (1996) 444

Ozone

- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436

Palladium

- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530

Phosphorus

- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556
- Phosphorus redistribution in the surface region of heavily phosphorus doped silicon, Y. Mizokawa, W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 561

Photochemistry

- In-situ IR and mass spectroscopic study of the Al(CH₃)₂H/a-Si:H reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575

Photoconductivity

- Oxide thickness dependence of photocurrent for the GeO₂/Ge film system, Y. Matsuo and K. Oishi 100/101 (1996) 248

Photoelectron spectroscopy

- Quantitative XPS: non-destructive analysis of surface nano-structures, S. Tougaard 100/101 (1996) 1
- Auger electron peaks of Cu in XPS, M. Jo and A. Tanaka 100/101 (1996) 11
- The influence of elastic scattering on the concentration dependence of the photoelectron line intensity, I.S. Tilinin, A. Jablonski and B. Lesiak-Orlowska 100/101 (1996) 20

- Comparison of AES chemical shifts with XPS chemical shifts, T. Sekine, N. Ikeo and Y. Nagasawa 100/101 (1996) 30
- Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra, P.C.J. Graat and M.A.J. Somers 100/101 (1996) 36
- A general procedure for extracting quantitative depth information from take-off-angle-resolved XPS and AES, W.H. Gries 100/101 (1996) 41
- XPS depth profiling by changing incident X-ray energy, H. Shimada, N. Matsubayashi, M. Imamura, T. Sato and A. Nishijima 100/101 (1996) 56
- UPS studies of conducting polymers: dopant effect on conjugated polymer systems sensitive to conductivity, S. Takemura, Y. Kitagawa, H. Kato and Y. Nakajima 100/101 (1996) 107
- Surface characterization of cell adhesion controlled polymer modified by ion bombardment, A. Nakao, M. Kaibara, M. Iwaki, Y. Suzuki and M. Kusakabe 100/101 (1996) 112
- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere, F. Yano, A. Hiraoka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui 100/101 (1996) 138
- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwasa and T. Arakawa 100/101 (1996) 147
- The surface and interface reaction of metal thin film on sapphire substrate, H.J. Kang, C.H. Kim, N.S. Park and M.W. Kim 100/101 (1996) 160
- Adsorption and thermal decomposition of diethyltellurium on GaAs(100), S.I. Gheyas, M. Nishio, T. Urisu and H. Ogawa 100/101 (1996) 211
- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
- Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis, M. Katoh, Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani 100/101 (1996) 226
- Charge-up and charge compensation on monochromatized X-ray photoelectron spectroscopic measurements of alumina and glass, H. Tomizuka and A. Ayame 100/101 (1996) 243
- Simulation of geometrical aberration and beam shape of scanning X-ray probe, H. Iwai, R. Oiwa, P.E. Larson and M. Kudo 100/101 (1996) 283
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS and RHEED, J. Murata, T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda 100/101 (1996) 417
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436
- Growth kinetics of thermal oxidation process on Si(100) by real time ultraviolet photoelectron spectroscopy, Y. Enta, Y. Takegawa, M. Suemitsu and N. Miyamoto 100/101 (1996) 449
- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454
- Co overlayer formation process on Si(100)- 2×1 studied by SR-PES, T. Jikimoto, C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 513
- Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino 100/101 (1996) 518
- Valence band structure of metal silicides modified by argon ion implantation, S. Yamauchi, Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 522
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556
- Phosphorus redistribution in the surface region of heavily phosphorus doped silicon, Y. Mizokawa, W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 561
- Photoluminescence enhancement of $(\text{NH}_4)_2\text{S}_x$ passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596
- XPS analysis of chemically etched II-VI semiconductor surfaces, A. Kita, M. Ozawa and C.D. Gutleben 100/101 (1996) 652

Plasma processing

- Heating effects on modifying carbon surface by reactive plasma, Y. Izumi, M. Katoh, T. Ohte, S. Ohtani, A. Kojima and N. Saitoh 100/101 (1996) 179
- Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis, M. Katoh, Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani 100/101 (1996) 226
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Low temperature etching of Si and PR in high density plasmas, M. Puech and Ph. Maquin 100/101 (1996) 579
- Deep trench etching in silicon with fluorine containing plasmas, R.D. Mansano, P. Verdonck and H.S. Maciel 100/101 (1996) 583
- Microwave plasma assisted LCVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643

Platinum

- Enhanced Raman scattering from copper phthalocyanine on Pt by use of a Weierstrass prism, M. Futamata, E. Keim, A. Bruckbauer, D. Schumacher and A. Otto 100/101 (1996) 60
- Surface structure analysis of dispersed metal sites on single crystal metal oxides by means of polarization-dependent total-reflection fluorescent EXAFS, W.-J. Chun, K. Asakura and Y. Iwasawa 100/101 (1996) 143

Polymers

- UPS studies of conducting polymers: dopant effect on conjugated polymer systems sensitive to conductivity, S. Takemura, Y. Kitagawa, H. Kato and Y. Nakajima 100/101 (1996) 107
- Surface characterization of cell adhesion controlled polymer modified by ion bombardment, A. Nakao, M. Kaibara, M. Iwaki, Y. Suzuki and M. Kusakabe 100/101 (1996) 112
- Photoresist characteristics of polyurea films prepared by vapor deposition polymerization. Depolymerization of polyurea, M. Iijima, M. Sato and Y. Takahashi 100/101 (1996) 120
- Molecular orientation of polyimide films determined by an optical retardation method, K. Sakamoto, R. Arafune, S. Ushioda, Y. Suzuki and S. Morokawa 100/101 (1996) 124

Pulsed laser ablation

- Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of CdWO₄(010), K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264

Raman scattering

- XPS depth profiling by changing incident X-ray energy, H. Shimada, N. Matsubayashi, M. Imamura, T. Sato and A. Nishijima 100/101 (1996) 56
- Enhanced Raman scattering from copper phthalocyanine on Pt by use of a Weierstrass prism, M. Futamata, E. Keim, A. Bruckbauer, D. Schumacher and A. Otto 100/101 (1996) 60

Scanning tunneling microscopy

- Development of ion irradiation system for in situ observation of ion irradiated semiconductor surfaces by ultra high vacuum scanning tunneling microscope, J. Ishikawa, H. Tsuji, K. Kameyama, S. Shimada and Y. Gotoh 100/101 (1996) 370
- Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- STM analysis of wet-chemically prepared H-Si(001) surface, Y. Morita and H. Tokumoto 100/101 (1996) 440

Schottky barrier

- Electrical properties of metal/Si_{1-x}Ge_x/Si(100) heterojunctions, H. Shinoda, M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596

Secondary ion mass spectrometry

- High depth resolution depth profiling of metal films using SIMS and sample rotation, D.E. Sykes, A. Chew, J. Hems and K. Stribley 100/101 (1996) 77
- Secondary ion emission from Langmuir-Blodgett (LB) films investigated by time-of-flight secondary ion mass spec-

- trometry, M. Kudo, S. Yamada, S. Yoshida, T. Watanabe and T. Hoshi 100/101 (1996) 129
- Surface oxygen and electrical resistance of $\text{YBa}_2\text{Cu}_3\text{O}_x$, S. Saito, M. Ishihara, T. Tani, T. Maeda, N. Watanabe, I. Rittaporn and N. Koshizuka 100/101 (1996) 260
- Molecular beam epitaxy of GaAs/ $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{In}_y\text{Ga}_{1-y}\text{As}$ heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556
- Phosphorus redistribution in the surface region of heavily phosphorus doped silicon, Y. Mizokawa, W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 561
- Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- ### Selenium
- Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4:\text{Ce}$ thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639
- XPS analysis of chemically etched II-VI semiconductor surfaces, A. Kita, M. Ozawa and C.D. Gutleben 100/101 (1996) 652
- ### Semiconductors
- Real-time analysis of III-V-semiconductor epitaxial growth, W. Richter and J.-T. Zettler 100/101 (1996) 465
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Technology development strategies for the 21st century, M.T. Bohr 100/101 (1996) 534
- A theoretical analysis of temperature dependence on hydrogenated amorphous silicon thin-film transistors with the consideration of resistance of the a-Si:H film layer as a function of temperature, B.-Y. Chen, J.-R. Chen, F.-L. Jenq and C.-S. Hong 100/101 (1996) 601
- ### Silicides
- Valence band structure of metal silicides modified by argon ion implantation, S. Yamauchi, Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 522
- Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- ### Silicon
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Damage profiling of Ar^+ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere, F. Yano, A. Hiraoka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui 100/101 (1996) 138
- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwaso and T. Arakawa 100/101 (1996) 147
- Structural fluctuation of SiO_2 network at the interface with Si, Y. Sugita, S. Watanabe, N. Awaji and S. Komiya 100/101 (1996) 268
- Ultrahigh vacuum system for atomic-scale planarization of 6 inch Si(001) substrate, K. Idota, M. Niwa and I. Sumita 100/101 (1996) 311
- Dissociative scattering of low-energy SiF_3^+ and SiF^+ ions (5–200 eV) on Cu(100) surface, H. Yamamoto, Y. Baba and T.A. Sasaki 100/101 (1996) 333
- CBE-grown high-quality GaAs on Si substrate, H. Uchida, M. Adachi, H. Nishikawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 399
- Infrared external reflection spectroscopy of self-assembled monolayer films on Si substrate with a buried metal layer

- (BML) structure, Y. Kobayashi and T. Ogino 100/101 (1996) 407
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- Initial oxidation of Si(311) surfaces studied by high-resolution electron energy loss spectroscopy, H. Ikeda, T. Yamada, K. Hotta, S. Zaima and Y. Yasuda 100/101 (1996) 431
- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436
- STM analysis of wet-chemically prepared H-Si(001) surface, Y. Morita and H. Tokumoto 100/101 (1996) 440
- Oxygen adsorption on hydrogen-preadsorbed Si(111)7 × 7 observed by second harmonic generation (SHG), K. Nakamura, S. Ichimura and H. Shimizu 100/101 (1996) 444
- Growth kinetics of thermal oxidation process on Si(100) by real time ultraviolet photoelectron spectroscopy, Y. Enta, Y. Takegawa, M. Suemitsu and N. Miyamoto 100/101 (1996) 449
- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454
- Doping dependence of second harmonic generation from native oxide/Si(111) interfaces, H. Hirayama, K. Watanabe and M. Kawada 100/101 (1996) 460
- Epitaxial growth of GaAs on HF-treated Si substrates, Y. Uchida, J. Minemura, Y. Yazawa and T. Warabisako 100/101 (1996) 478
- GaAs-based LED on Si substrate with GaAs islands active region by droplet-epitaxy, Y. Hasegawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 482
- Novel method of strain-relaxed Si_{1-x}Ge_x growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503
- Co overlayer formation process on Si(100)-2 × 1 studied by SR-PES, T. Jikimoto, C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 513
- Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino 100/101 (1996) 518
- Electrical properties of metal/Si_{1-x}Ge_x/Si(100) heterojunctions, H. Shinoda, M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556
- Phosphorus redistribution in the surface region of heavily phosphorus doped silicon, Y. Mizokawa, W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 561
- Selective epitaxial Si based layers and TiSi₂ deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- In-situ IR and mass spectroscopic study of the Al(CH₃)₂H/a-Si:H reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575
- Low temperature etching of Si and PR in high density plasmas, M. Puech and Ph. Maquin 100/101 (1996) 579
- Deep trench etching in silicon with fluorine containing plasmas, R.D. Mansano, P. Verdonck and H.S. Maciel 100/101 (1996) 583
- A theoretical analysis of temperature dependence on hydrogenated amorphous silicon thin-film transistors with the consideration of resistance of the a-Si:H film layer as a function of temperature, B.-Y. Chen, J.-R. Chen, F.-L. Jenq and C.-S. Hong 100/101 (1996) 601
- Infrared study of chemistry of Si surfaces in etching solution, M. Niwano, T. Miura, R. Tajima and N. Miyamoto 100/101 (1996) 607
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621

Silicon nitride

- Photoluminescence enhancement of (NH₄)₂S_x passivated InP surface by

- rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592

Silicon oxide

- Structural fluctuation of SiO₂ network at the interface with Si, Y. Sugita, S. Watanabe, N. Awaji and S. Komiya 100/101 (1996) 268
- Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- Doping dependence of second harmonic generation from native oxide/Si(111) interfaces, H. Hirayama, K. Watanabe and M. Kawada 100/101 (1996) 460

Sputter deposition

- Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere, B. Yea, R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara 100/101 (1996) 365

Sputtering

- Damage profiling of Ar⁺ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Processes in low-energy ion-surface collisions: preferential sputtering, defect and adatom formation, H. Gnaser 100/101 (1996) 316
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329

Steel

- Effect of different surface treatments on the precipitation of boron nitride for stainless steel SUS304, Y. Suzuki, T. Homma, M. Minato and Y. Itoh 100/101 (1996) 165

Strontium

- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Preparation of blue-emitting SrGa₂Se₄:Ce thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tat-

- suoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639

- Preparation and photoluminescent characteristics of Zn_xSr_{1-x}S:Ce thin films, S.T. Lee, M. Kitagawa, K. Ichino and H. Kobayashi 100/101 (1996) 656

Sulphur

- Correlation between cathodoluminescence and structural defects in ZnS/GaAs(100) and ZnSe/GaAs(100) studied by transmission electron microscopy, T. Mitsui, N. Yamamoto, J. Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue 100/101 (1996) 625
- Preparation and photoluminescent characteristics of Zn_xSr_{1-x}S:Ce thin films, S.T. Lee, M. Kitagawa, K. Ichino and H. Kobayashi 100/101 (1996) 656

Superconductors

- Characterization of freeze-dried powders prepared by alkoxide route for YBCO superconductors, T. Tachiwaki, J. Sugimoto, T. Ito and A. Hiraki 100/101 (1996) 272

Superconductivity

- Surface oxygen and electrical resistance of YBa₂Cu₃O₇, S. Saito, M. Ishihara, T. Tani, T. Maeda, N. Watanabe, I. Rittaporn and N. Koshizuka 100/101 (1996) 260
- Investigation of the physical and chemical interaction of a low energy oxygen ion beam with oxide superconducting films, G. Pindoria, M. Badaye, F. Wang, K. Kawaguchi and T. Morishita 100/101 (1996) 347

Superlattices

- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503

Surface composition

- Novel method of strain-relaxed Si_{1-x}Ge_x growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487

Surface morphology

- Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487

Tantalum

- Soft X-ray emissions by highly charged ions on solid surfaces: Mo and Ta surfaces, T. Emoto, K. Komatsu, A. Ichimiya, S. Ninomiya and M. Sekiguchi 100/101 (1996) 355

Tellurium

- Water vapor effects on the TeO_2/Te thin film conductance, S. Suehara, T. Hatano and A. Nukui 100/101 (1996) 252
- Growth of high-quality ZnTe layers by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 647
- XPS analysis of chemically etched II-VI semiconductor surfaces, A. Kita, M. Ozawa and C.D. Gutleben 100/101 (1996) 652

Thallium

- Thermal positive ion production from thallium chloride molecules impinging upon a tungsten surface heated in high vacua, H. Kawano, K. Ohgami and N. Serizawa 100/101 (1996) 199

Thermal desorption

- Temperature-programmed desorption of positive ions and neutral molecules from alkali halide layers deposited on a metal surface, H. Kawano, S. Kamidoi, H. Shimizu, K. Ushimaru and H. Asada 100/101 (1996) 174
- A modified surface of titanium and its vacuum characteristic, T. Homma, M. Minato, Y. Itoh, S. Akiya and T. Suzuki 100/101 (1996) 189
- Adsorption and thermal decomposition of diethyltellurium on GaAs(100), S.I. Gheyas, M. Nishio, T. Urisu and H. Ogawa 100/101 (1996) 211
- Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno 100/101 (1996) 232
- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS

- and RHEED, J. Murata, T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda 100/101 (1996) 417

- Photoluminescence enhancement of $(\text{NH}_4)_2\text{S}_x$ passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592

Thin films

- Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra, P.C.J. Graat and M.A.J. Somers 100/101 (1996) 36
- High depth resolution depth profiling of metal films using SIMS and sample rotation, D.E. Sykes, A. Chew, J. Hems and K. Stribley 100/101 (1996) 77
- Structural properties of epitaxially grown perfluoro *n*-alkane thin films prepared by vapor deposition, K. Ishida, T. Horiuchi, S. Kai and K. Matsushige 100/101 (1996) 116
- Molecular orientation of polyimide films determined by an optical retardation method, K. Sakamoto, R. Arafune, S. Ushioda, Y. Suzuki and S. Morokawa 100/101 (1996) 124
- Water vapor effects on the TeO_2/Te thin film conductance, S. Suehara, T. Hatano and A. Nukui 100/101 (1996) 252
- Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere, B. Yea, R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara 100/101 (1996) 365
- Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino 100/101 (1996) 518
- High-rate deposition of high-quality Cu film with LPCVD, K. Numajiri, T. Goya, R. Tobe, O. Okada, N. Hosokawa, C. Mu, N. Cox, C. Scott and J. Yu 100/101 (1996) 541
- Low pressure MOCVD of TiN thin films, S.W. Kim, H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa 100/101 (1996) 546
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
- Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4:\text{Ce}$ thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639

- Microwave plasma assisted LCVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643

Time of flight techniques

- Apparatus for positron-annihilation-induced Auger electron spectroscopy with a pulsed positron beam, R. Suzuki, T. Ohdaira, T. Mikado, H. Ohgaki, M. Chiwaki and T. Yamazaki 100/101 (1996) 297

Tin

- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Sn segregation to the low index surfaces of a copper single crystal, J. du Plessis and E.C. Viljoen 100/101 (1996) 222

Tin oxide

- Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere, B. Yea, R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara 100/101 (1996) 365

Titanium

- The surface and interface reaction of metal thin film on sapphire substrate, H.J. Kang, C.H. Kim, N.S. Park and M.W. Kim 100/101 (1996) 160
- A modified surface of titanium and its vacuum characteristic, T. Homma, M. Minato, Y. Itoh, S. Akiya and T. Suzuki 100/101 (1996) 189
- Effect of gas adsorption on the segregation behavior of substrate Cu on Ti film, M. Yoshitake and K. Yoshihara 100/101 (1996) 203
- Electrical properties of metal/Si_{1-x}Ge_x/Si(100) heterojunctions, H. Shinoda, M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526
- Selective epitaxial Si based layers and TiSi₂ deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566

Titanium nitride

- Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno 100/101 (1996) 232
- Low pressure MOCVD of TiN thin films, S.W. Kim, H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa 100/101 (1996) 546

Tungsten

- Thermal positive ion production from thallium chloride molecules impinging upon a tungsten surface heated in high vacuum, H. Kawano, K. Ohgami and N. Serizawa 100/101 (1996) 199
- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
- Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of CdWO₄(010), K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264

Water

- Water vapor effects on the TeO₂/Te thin film conductance, S. Suehara, T. Hatano and A. Nukui 100/101 (1996) 252

Work function

- Quantitative relationship between the work function and transfer ratio of a potassium-adsorbed MIM cathode, T. Kusunoki and M. Suzuki 100/101 (1996) 207

Xenon

- Angular distribution of particles sputtered from GaAs by Ar⁺ and Xe⁺ ion bombardment, T. Aoyama, M. Tanemura and F. Okuyama 100/101 (1996) 351

X-ray absorption

- Surface structure analysis of dispersed metal sites on single crystal metal oxides by means of polarization-dependent total-

- reflection fluorescent EXAFS, W.-J. Chun, K. Asakura and Y. Iwasawa 100/101 (1996) 143

X-ray diffraction

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